Charles University Prague Institute of Particle and Nuclear Physics

Laser Tests of Silicon Detectors

Peter Kodyš, Zdeněk Doležal, Jan Brož, Pavel Řezníček, Zbyněk Drásal, Pavel Bažant, Jan Poslušný



Tests on beam <-> beta tests <-> laser tests

• Tests on beam of high energy particles (beam tests):

Most similar conditions to real experiment

Available only few times in year and complicated organization

High coast

• Tests used β particles from radioactive sources:

Lower coast and good availability, used real particles

Wide spectra of energies without their measurement possibility

Unknown interaction point between particle and sensor, no space resolution information

• Tests with laser light:

Exact precise space resolution, lower coast, good availability Depth penetration setting using different light energy (wavelength) Complication on absolute efficiency measurement from energy from photon beam

Laser tests

Basic differences between particles and light beam in silicon:

- laser tests used beam of light with nonzero width
- different method of electron generation

Some effects missing:

- δ drift electrons
- energy of particles

Some effects added:

primary and secondary reflections



Silicon Microstrip Detector

Principle:

>collection of charge released in the depleted volume of a reverse biased diode

- >spatial resolution through segmentation of diode
- ➢p strips on n substrate
- >AC coupling to keep leakage current away from read-out electronics
- biasing through polysilicon or implanted resistors
- Irradiation in SCT volume up to 1.2x10¹⁴ 1-MeV-n/cm² for 10 years of LHC running

Properties:

leakage current
depletion voltage and substrate resistivity
interstrip capacitance
backplane capacitance
crystal orientation
charge collection
signal to noise





Charles University
Prague
Charge genera

Charge generation in silicon induced by particles





Charge generation in silicon induced by laser beam





Most typical arrangement of laser tests





Response of testing modules



Sum of signal of 12 adjacent strips show that collected signal in one channel is 85% from whole collected charge in detector.

Typical response from few channels if laser beam moves across strips in best focused point.



Laser tests - focusing



Principle used for laser focusing

Laser tests - focusing

Main conclusion: there is possibility to tune laser focusing to smallest spot using reflectivity from strip metal material, sensitivity of focusing of our type of laser output is very high, focus range is less 50 μ m (from factory is declared good focus range about 1 mm).





Peter Kodyš, Paris, February 2006



Laser Tests - Applications

- Numerous tests of ATLAS end cap SCT modules were developed and performed:
- The bond mixing test done up to 30 minutes per detector test for production modules
- The channels from mask file (bad channels) tested independently using two methods
- Punch through (pin hole) channels test (gain confirmation) for response
- Pulse shape reconstruction
- Test of homogeneity of response from detector in full area is possible
- Detail response vs. inter-strip position
- Bias scan of detectors
- Temperature scan
- Spatial resolution of noise bump-strips on CiS detectors was checked and measured



Pulse shape reconstruction





Reflectivity measurement





Optical properties



Plots comparing reflectivity measurement and calculation from thickness of layers in range 300 - 1100nm of wavelength



Absolute response measurements are problematic: deposition of defined charge in the sensor is difficult because of many optical effects: - part of light is reflected

- sometime transparent layers are not homogenous because technology of covering use also transport of atoms between layers so borders between layers are gradients and no steps

- refractive index for some materials must be measured because big spread of value depends of using deposition and surface polishing technology

- thick and transparent substrates gives hardly defined conditions for reflectivity calculation

- the best is use the same laser beam for also reflectivity measurement (method of this is on the way)

Refractive index and
 200 μm
 thickness of layers was
 measured on spot in range
 300 - 800nm of wavelength.



New Tests

- large area diodes tests
- depfet strustures

 $\begin{array}{l} \mbox{Stability of laser pulse:} \\ \mbox{Amplitude: } \sigma < 1.5\% @ 1.8 \mbox{MeV deposited} \\ \mbox{Timing jitter: } \sigma < 0.4 \mbox{ns @ 32 \mbox{MeV deposited}} \end{array}$





Response of Si pad detector for 1060nm light wavelength

Arrangement of tests



Response of DEPFET detector

Peter Kodyš, Paris, February 2006

Laser Tests And Simulations

350

300

250

2D distr. of generated e-h pairs \approx 4fC, α = 30°, div = 0.5°

Light propagation in silicon

150

200

250

300

How is signal on detector created

2

0.5

40

³⁰20₁₀

10 0 y[µm]-10 -20 -30 -40



100 150

200

250

10 t[ns] 12

i(t)[µA] -0.02

-0.04

-0.06

Space Resolutions Measurements





Cooperation

- Help in building of new laser test laboratories: MPI Mnichov, University Freiburg
- Looking for examples for testing around
- Cooperation with:
 - ÚRE AVČR Prague
 - University of Freiburg
 - MPI Mnichov
 - University of Bonn
 - University of Lancaster
 - University of Bari
 - Lappeenranta University of Technology





Laser tests are useful in:

- precise space resolution studies
- time walk and time shape measurements
- functionality of problematic part of detectors
- surface charge collection and deep charge generation from 4 mm@650nm up to 1mm@1060nm

Quality of tests depends from:

- top layers: thickness, refractive index, surface quality
- geometry of pads on top, their material, surface of them, protected layers
- laser light beam quality, coherent properties, long time stability, aperture, wavelength





Laser test are:

 extremely useful for tuning of individual sensor and readout settings to find optimal working parameters

 good for comparison between the same type of detectors with exactly the same top surface properties

 of limited use in absolute measurement of efficiency of semiconductor detectors (under study)



Place Of Laser Tests



Clean room in Prague Charles University with laser black box and readout electronics stands

Visual inspection place





Laser spot on detectors in 1060nm and 660 nm wavelength, strip pitch is 80 µm



Black box for laser test measurements

Peter Kodyš, Paris, February 2006



Charles University

Prague

Arrange ment in black box



3D2R Laser System





Lighting to detector

3D2R moving system

> Tilting of laser beam before mounting of detector



This document was created with Win2PDF available at http://www.win2pdf.com. The unregistered version of Win2PDF is for evaluation or non-commercial use only.